

Product data sheet

#### 1. **Product profile**

#### 1.1 General description

Passivated, sensitive gate triacs in a SOT54 plastic package

#### 1.2 Features and benefits

Designed to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 1.3 Applications

General purpose switching and phase control

#### 1.4 Quick reference data

- V<sub>DRM</sub> ≤ 600 V (BT131-600)
- $I_{T(RMS)} \le 1 A$
- $V_{DRM} \le 800 \text{ V (BT131-800)}$
- $I_{TSM} \le 12.5 A$

#### **Pinning information** 2.

Table 1. **Pinning** 

| Pin | Description          | Simplified outline | Symbol       |
|-----|----------------------|--------------------|--------------|
| 1   | main terminal 2 (T2) |                    | N.I.         |
| 2   | gate (G)             |                    | T2—T1        |
| 3   | main terminal 1 (T1) |                    | `G<br>sym051 |
|     |                      | SOT54 (TO-92)      |              |



# 3. Ordering information

Table 2. Ordering information

| Type number | Package |   |         |  |  |
|-------------|---------|---|---------|--|--|
|             | Name    | Description   | Version |  |  |
| BT131-600   | TO-92   | plastic single-ended leaded (through hole) package; 3 leads | SOT54   |  |  |
| BT131-800   |         |   |         |  |  |

# 4. Limiting values

#### Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                            | Conditions  | Min          | Max  | Unit             |
|---------------------|--------------------------------------|---|--------------|------|------------------|
| $V_{DRM}$           | repetitive peak off-state voltage    |   |              |      |                  |
|                     | BT131-600                            |   | <u>[1]</u> - | 600  | V                |
|                     | BT131-800                            |   | -            | 800  | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                 | all conduction angles;<br>T <sub>lead</sub> = 51.2 °C;<br>see <u>Figure 1</u> , <u>4</u> and <u>5</u> | -            | 1    | А                |
| I <sub>TSM</sub>    | non-repetitive peak on-state current | half sine wave; $T_j = 25 ^{\circ}\text{C}$ prior to surge; see Figure 2 and 3                        |              |      |                  |
|                     |                                      | t = 20 ms   | -            | 12.5 | Α                |
|                     |                                      | t = 16.7 ms   | -            | 13.8 | Α                |
| l <sup>2</sup> t    | I <sup>2</sup> t for fusing          | t = 10 ms   | -            | 1.28 | A <sup>2</sup> s |
| dI <sub>T</sub> /dt | rate of rise of on-state current     | $I_{TM} = 1.5 \text{ A}; I_G = 20 \text{ mA};$<br>$dI_G/dt = 200 \text{ mA/}\mu\text{s}$              |              |      |                  |
|                     |                                      | T2+ G+  | -            | 50   | A/μs             |
|                     |                                      | T2+ G-  | -            | 50   | A/μs             |
|                     |                                      | T2- G-  | -            | 50   | A/μs             |
|                     |                                      | T2- G+  | -            | 10   | A/μs             |
| $I_{GM}$            | peak gate current                    |   | -            | 2    | Α                |
| $P_{GM}$            | peak gate power                      |   | -            | 5    | W                |
| $P_{G(AV)}$         | average gate power                   | over any 20 ms period   | -            | 0.1  | W                |
| T <sub>stg</sub>    | storage temperature                  |   | -40          | +150 | °C               |
| Tj                  | junction temperature                 |   | -            | 125  | °C               |

<sup>[1]</sup> Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 3  $A/\mu s$ .

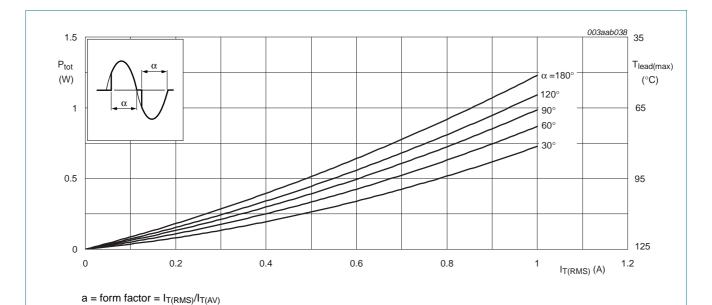


Fig 1. Total power dissipation as a function of average on-state current; maximum values

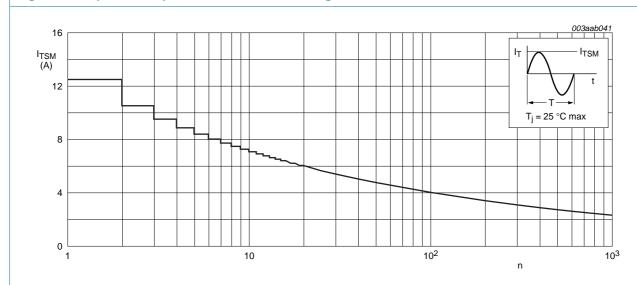
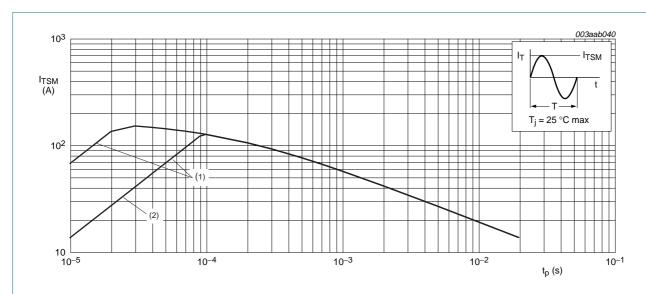


Fig 2. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

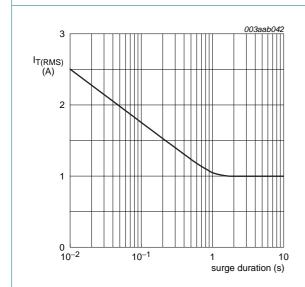
f = 50 Hz



 $t_p \le 20 \text{ ms}$ 

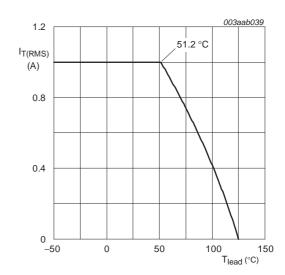
- (1) dI<sub>T</sub>/dt limit
- (2) T2- G+ quadrant

Fig 3. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values



f = 50 Hz;  $T_{lead} \le$  51.2 °C

Fig 4. RMS on-state current as a function of surge duration, for sinusoidal currents; maximum values



(1)  $T_{lead} = 51.2 \, ^{\circ}C$ 

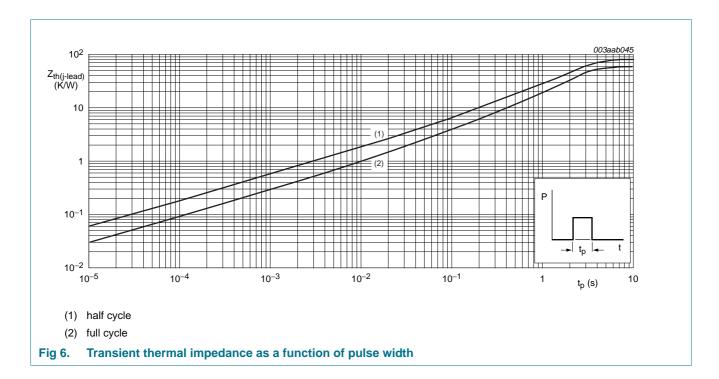
Fig 5. RMS on-state current as a function of lead temperature; maximum values

### 5. Thermal characteristics

Table 4. Thermal characteristics

| Symbol                               | Parameter                                   | Conditions   | Min   | Тур | Max | Unit |
|--------------------------------------|---|--------------|-------|-----|-----|------|
| R <sub>th(j-lead)</sub> thermal lead | thermal resistance from junction to         | full cycle   | -     | -   | 60  | K/W  |
|                                      | lead  | half cycle   | -     | -   | 80  | K/W  |
| $R_{th(j-a)}$                        | thermal resistance from junction to ambient | see Figure 6 | [1] _ | 150 | -   | K/W  |

[1] Mounted on a printed-circuit board; lead length = 4 mm

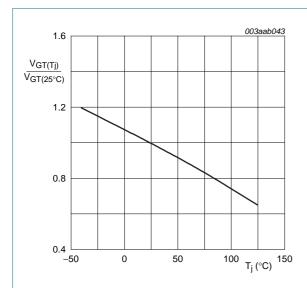


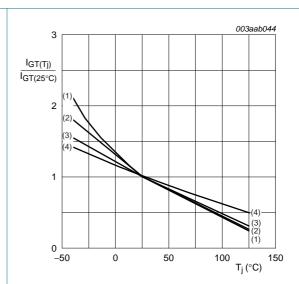
## 6. Characteristics

Table 5. Characteristics

 $T_i = 25 \,^{\circ}\text{C}$  unless otherwise stated.

| Symbol                | Parameter                             | Conditions   | Min | Тур | Max | Unit |
|-----------------------|---------------------------------------|--|-----|-----|-----|------|
| Static char           | acteristics                           |  |     |     |     |      |
| I <sub>GT</sub>       | gate trigger current                  | $V_D = 12 \text{ V; } I_T = 100 \text{ mA;}$<br>see Figure 8   |     |     |     |      |
|                       |                                       | T2+ G+   | -   | 0.4 | 3   | mA   |
|                       |                                       | T2+ G-   | -   | 1.3 | 3   | mA   |
|                       |                                       | T2- G-   | -   | 1.4 | 3   | mA   |
|                       |                                       | T2- G+   | -   | 3.8 | 7   | mA   |
| I <sub>L</sub>        | latching current                      | $V_D = 12 \text{ V; } I_{GT} = 100 \text{ mA;}$<br>see Figure 10   |     |     |     |      |
|                       |                                       | T2+ G+   | -   | 1.2 | 5   | mA   |
|                       |                                       | T2+ G-   | -   | 4   | 8   | mA   |
|                       |                                       | T2- G-   | -   | 1   | 5   | mA   |
|                       |                                       | T2- G+   | -   | 2.5 | 8   | mA   |
| l <sub>H</sub>        | holding current                       | $V_D = 12 \text{ V; } I_{GT} = 100 \text{ mA;}$<br>see Figure 11   | -   | 1.3 | 5   | mA   |
| $V_{T}$               | on-state voltage                      | I <sub>T</sub> = 1.4 A; see <u>Figure 9</u>  | -   | 1.2 | 1.5 | V    |
| $V_{GT}$              | gate trigger voltage                  | I <sub>T</sub> = 10 mA; gate open circuit; see Figure 7  |     |     |     |      |
|                       |                                       | $V_D = 12 \text{ V}; I_{GT} = 100 \text{ mA}$  | -   | 0.7 | 1.5 | V    |
|                       |                                       | $V_D = 400 \text{ V}; I_{GT} = 100 \text{ mA};$<br>$T_j = 125 \text{ °C}$                                  | 0.2 | 0.3 | -   | V    |
| I <sub>D</sub>        | off-state current                     | $V_D = V_{DRM(max)}$ ; $T_j = 125  ^{\circ}C$  | -   | 0.1 | 0.5 | mA   |
| Dynamic c             | haracteristics                        |  |     |     |     |      |
| dV <sub>D</sub> /dt   | rate of rise of off-state voltage     | $V_{DM} = 67 \% V_{DRM(max)}; T_j = 125 °C;$ exponential waveform; $R_{GK} = 1 k\Omega;$ see Figure 12     | 10  | 20  | -   | V/μs |
| dV <sub>com</sub> /dt | rate of change of commutating current | $V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C};$<br>$dI_{com}/dt = 0.5 \text{ A/ms}$                        | 2   | -   | -   | V/μs |
| t <sub>gt</sub>       | gate-controlled<br>turn-on time       | $I_{TM} = 1.5 \text{ A}; V_D = V_{DRM(max)};$<br>$I_G = 100 \text{ mA}; dI_G/dt = 5 \text{ A}/\mu\text{s}$ | -   | 2   | -   | μS   |

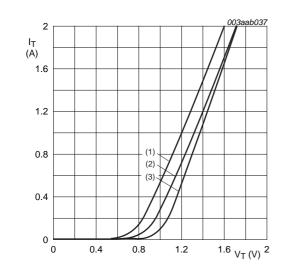




- (1) T2-G+
- (2) T2- G-
- (3) T2+ G-
- (4) T2+ G+

Fig 7. Normalized gate trigger voltage as a function of junction temperature





 $V_0 = 0.92 \text{ V}$ 

 $R_s = 0.4 \Omega$ .

- (1)  $T_j = 125$  °C; typical values
- (2)  $T_i = 125 \,^{\circ}C$ ; maximum values
- (3)  $T_i = 25 \,^{\circ}C$ ; maximum values

Fig 9. On-state current characteristics

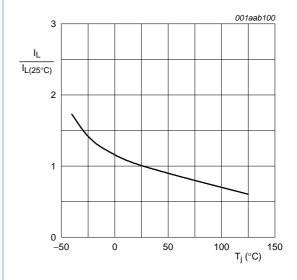


Fig 10. Normalized latching current as a function of junction temperature

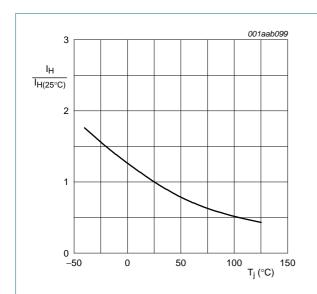


Fig 11. Normalized holding current as a function of junction temperature

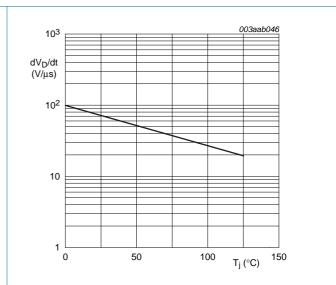


Fig 12. Rate of rise of off-state voltage as a function of junction temperature; minimum values

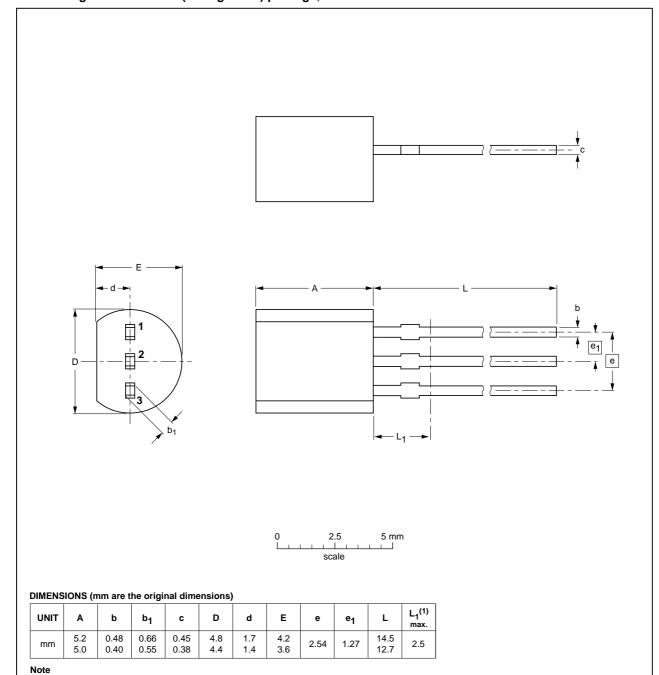
# 7. Package information

Epoxy meets requirements of UL94 V-0 at ½ inch.

## **Package outline**

#### Plastic single-ended leaded (through hole) package; 3 leads

SOT54



1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

| OUTLINE |     | REFER | ENCES  | EUROPEAN ISSUE D | ISSUE DATE                      |
|---------|-----|-------|--------|------------------|---------------------------------|
| VERSION | IEC | JEDEC | JEITA  | PROJECTION       | ISSUE DATE                      |
| SOT54   |     | TO-92 | SC-43A |                  | <del>04-06-28</del><br>04-11-16 |

Fig 13. Package outline SOT54 (TO-92)

# 9. Revision history

### Table 6. Revision history

| Document ID      | Release date                      | Data sheet status                                      | Change notice       | Supersedes           |
|------------------|-----------------------------------|--|---------------------|----------------------|
| BT131_SER v.9    | 20111109                          | Product data sheet                                     | -                   | BT131_SER v.8        |
| Modifications:   |                                   | f this data sheet has been rede<br>NXP Semiconductors. | esigned to comply w | ith the new identity |
|                  | <ul> <li>Legal texts h</li> </ul> | ave been adapted to the new                            | company name whe    | re appropriate.      |
| BT131_SER v.8    | 20050909                          | Product data sheet                                     | -                   | BT131_SERIES v.7     |
| BT131_SERIES v.7 | 20040101                          | Product specification                                  | -                   | BT131_SERIES v.6     |
| BT131_SERIES v.6 | 20030801                          | Product specification                                  | -                   | BT131_SERIES v.5     |
| BT131_SERIES v.5 | 20001201                          | Product specification                                  | -                   | BT131_SERIES v.4     |
| BT131_SERIES v.4 | 20000501                          | Product specification                                  | -                   | BT131_SERIES v.3     |
| BT131_SERIES v.3 | 19980401                          | Product specification                                  | -                   | -                    |

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#### 10.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
| Product [short] data sheet     | Production        | This document contains the product specification.                                     |

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
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BT131\_SER

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NXP Semiconductors

BT131 series

#### **Triacs logic level**

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# **BT131 series**

**Triacs logic level** 

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